Appendix A Student Declaration of Academic Integrity

Students may be required to submit work for assessment in a variety of means, for example physical submission or electronic submission through Moodle. In all cases students must make a declaration of academic integrity, either by physically completing such a declaration and submitting it with their assignment or engaging appropriately with the electronic version of the student declaration. Assignments submitted such that the form has not been included, or the electronic equivalent has been circumvented, will not be accepted.

Declaration

Name: Ankit Bose

Student ID Number: 14210387

Programme: MENC (Masters Electronic Systems)

Module Code: EE506

Assignment Title: EE506 Assignment

Submission Date: 24-April-2015

I understand that the University regards breaches of academic integrity and plagiarism as grave and serious.

I have read and understood the DCU Academic Integrity and Plagiarism Policy . I accept the penalties that may be imposed should I engage in practice or practices that breach this policy.

I have identified and included the source of all facts, ideas, opinions, viewpoints of others in the assignment references. Direct quotations from books, journal articles, internet sources, module text, or any other source whatsoever are acknowledged and the sources cited are identified in the assignment references.

I declare that this material, which I now submit for assessment, is entirely my own work and has not been taken from the work of others save and to the extent that such work has been cited and acknowledged within the text of my work.

I have read and understood the DCU library referencing guidelines (available at: <u>http://www.library.dcu.ie/LibraryGuides/DCU Library Guide to Harvard Style of Citing &</u> <u>Referencing/player.html</u> Referencing/player.html accessed 9th January 2013) and/or recommended in the assignment guidelines and/or programme documentation.

By signing this form or by submitting this material online I confirm that this assignment, or any part of it, has not been previously submitted by me or any other person for assessment on this or any other course of study.

By signing this form or by submitting material for assessment online I confirm that I have read and understood DCU Academic Integrity and Plagiarism Policy (available at: http://www4.dcu.ie/registry/examinations/plagiarism.pdf accessed 9th January 2013)

Name: Ankit Bose

Date: 24-April-2015

Report of Suspected Plagiarism / Breach of Academic Integrity

att and <u>entities of the set of the set of the section</u> de = 0 r 0 to i dependency De capacitien for Abrenkisto 1.1) <u>dN = I = A(N-N)R - N</u> ME READ dit = <u>A(N-N)R - N</u> conserved to det to a there is the and the served of at S (NON) Bro Balt Bin wild natu The symbols in above set of equations mean the follows:-D I = bias current applied to the claser. A = Coefficient of gain Te = carrier lifetime Tp = photon difetime N = carrier number P = photon number β = Spontaneous emission coupling No = carrier number at transparency dN = Rate of equation for N $\frac{dP}{d+}$ = Rate of equation for P

1.2) To calculate the threshold current, we assume the rate equations to be in steady state condition i.e. d=0 no deme dependance. Since the optical gain is linear with pumping, i.e. the current injected and therefore the carrier number. It is possible the approximate the gain as a linear function of the carrier, $G = A(N - N_0)$ The expression for threshold current is ochieved by considering that GP>> BN where GPis stimulated emission & <u>PN</u> is spontaneous emission. The spontaneous emission is neglected & Gain becomes equal to the losses. i.e. $A(N-N_0) = \frac{1}{T_p}$ $N = N_0 + \frac{1}{A c_0}$ Using the above value N in carrier rate equation $\frac{I}{C} - \frac{N}{Z_{e}} \ge A(N-N_{0})^{2} \implies \frac{I}{F} = \frac{I}{C} - \frac{1}{T_{e}} \left(\frac{N_{0} + 1}{AT_{p}} \right) \ge \frac{C}{T_{p}}$ ' P can be expressed as $P = \frac{T_P}{C} (I - I_S)$ where I_S is the threshold current. with $E = \frac{T_P}{C} (I - I_S)$ $\frac{I_{SZ}}{\gamma_{e}} \left(\frac{N_{0} + 1}{A\gamma_{e}} \right)$ By inserting the given values in the above equation, we get $I_5 \ge 14.39 \text{ mA}$

1-3) Below the threshold current, the number of carriers keeps increasing with the increase in bias current according to this expression: CM MG = D $N = \frac{\gamma_e}{e}I$ Above the threshold current, the member of carriers is damped at a value No + 1 when the gain is equal to the losses. ATp As the bias current increases, the carrier number is fixed and the gain will not increase. So, the encess of carriers are directly used for stimulated emission. step the above rates to can reparce the expected $\left(\frac{1+m}{p}\right) = \frac{1}{p} = \frac{1}{p}$ Econda supervise as Po Er (I-I) " threehold current work to

2.1) For small signal analysis on steady state good tatitos quantities N, P, I, we unteroduce a perturbation of the current SI, which results in perturbation of the carrier number SN and photon number SP. Instead of I we use I + SI, of N, N+SN, of P, P + SP & the rate equation decomes: STATS <u>dN+SN = I+SI</u> A(N+SN-ND)(F+SP) - N+SN dt <u>G</u> $\frac{d\overline{P}+SP}{dt} = A(\overline{N}+SN-N_0)(\overline{P}+SP) - \frac{\overline{P}+SP}{T_p} + \beta \frac{\overline{N}+SN}{T_e}$ In order to develop these equations, the second order expressions i.e. SN, SP are neglected and set to zero. Therefore, the Equation for pertostation tocanse. Atro, it is Since the analysis is carried out above threshold i.e. $A(\overline{N}-N_0) = 1$, the above equations can be re-written as: $\frac{d(sN)}{dt} = \frac{SI}{e} - (\overline{AP} + \underline{I}) sN - \frac{SP}{T_p}$ $\frac{d(sP)}{dt} = \overline{AP} sN$ d(SP) z AFSN dt These equations can be expressed in the matrix form as: Scanned by CamScanner

2.2) From the above equation in 2.1, we found that

$$\begin{pmatrix}
\frac{d}{dt} SN \\
\frac{d}{dt} \\
\frac{d}{dt}
\end{pmatrix} = \begin{pmatrix}
-(A\vec{P}+1) & -\frac{1}{T_{P}} \\
\frac{d}{T_{e}} & T_{P} \\
A\vec{P} & 0
\end{pmatrix} \begin{pmatrix}
SN \\
+\begin{pmatrix}
\frac{8T}{e} \\
e \\
0
\end{pmatrix}$$
where $\vec{N} = \begin{pmatrix}
-(A\vec{P}+1) & -1 \\
T_{e} \\
T_{P} \\
T_{P} \\
T_{P} \\
A\vec{P} \\
0
\end{pmatrix}$

2.3) Junction of SI, the equation in Fourier domain can be written os ! $\begin{pmatrix} j \Omega J (A\overline{P} + L) \\ \overline{L_e} \\ -A\overline{P} \\ \end{pmatrix} \begin{pmatrix} J \Omega J \\ \overline{L_e} \\ J \Omega \end{pmatrix} \begin{pmatrix} \overline{S} \overline{N} \\ \overline{S} \overline{P} \\ S\overline{P} \end{pmatrix} = \begin{pmatrix} \overline{S} \overline{L_e} \\ \overline{S} \overline{P} \\ 0 \end{pmatrix}$ We could consider: $M = \begin{pmatrix} j \Omega + (A\bar{P} + \bot) \\ T_{e} \end{pmatrix} \begin{pmatrix} J \\ T_{p} \end{pmatrix} \\ -A\bar{P} \end{pmatrix} \begin{pmatrix} J \Omega \\ T_{p} \end{pmatrix}$ (M3) b $\frac{1}{2} \begin{pmatrix} \overline{SN} \\ \overline{SP} \end{pmatrix} = \overline{M}^{-1} \begin{pmatrix} \overline{SI}_{e} \\ \overline{O} \end{pmatrix}$ $\frac{2}{2} M \text{ is expressed as } \begin{pmatrix} a & b \\ C & d \end{pmatrix} \text{ then,}$ $M^{-1} = \frac{1}{ad - bc} \begin{pmatrix} d & -b \\ -c & a \end{pmatrix}$ $M^{-1} = \frac{1}{ad - bc} \begin{pmatrix} j -c & a \end{pmatrix}$ $= -2^{2} + \frac{A\overline{P}}{Z_{p}} + j \cdot 2\left(\frac{A\overline{P} + 1}{Z_{e}}\right) \begin{pmatrix} j \cdot 2 & -\frac{1}{Z_{p}} \\ A\overline{P} & j \cdot 2 + \left(\frac{A\overline{P} + 1}{Z_{e}}\right) \end{pmatrix}$

 $\omega_R^2 = \frac{P\bar{P}}{T_P}$ and $\frac{2}{T_R} = \frac{P\bar{P} + 1}{T_R}$ Up is the relanation oscillation and 2 is the damping The coefficient. 1. Sh 7 DEL $\frac{SN}{-\Omega^{2} + \frac{A\overline{P}}{T_{0}} + \int \Omega \left(\frac{A\overline{P}}{Z_{p}} \right) \frac{ST}{C}}$ $\widetilde{SN} = \frac{j\Omega}{-\Omega^2 + \omega_R^2 + j\Omega \frac{2}{Z_R}} \frac{\delta I}{C}$ $\frac{1}{2} \cdot \frac{\delta \bar{P} - \alpha^2 + A \bar{P}}{2\alpha} + j \alpha \left(A \bar{P} + j \right) \frac{\delta \bar{L}}{2\alpha}$ $\widetilde{SP} = \frac{\omega_{R}^{2} T_{P}}{-\Omega^{2} + \omega_{R}^{2} + \int \Omega \frac{2}{T_{r}}} \frac{SI}{C}$

 $\frac{3}{N} = \left(\frac{ne}{hc/\lambda}\right)^2 P_s^2$ $\left(\begin{array}{c} 2e\left(\frac{ne}{kc/\lambda}\right)^{R_{s}} + \frac{4kT}{R_{c}}\right)\Delta f$ 3.1) The given values are k = 1,38×10-235/K y = 0.85 e= 1.6×10-19C T = 300K L= 6.62×10-34 J. Rr = SOIL C= 3×10 m/s Df= 20×10 Hz >= 1.55 × 10 m $P_{s} = -3dBm$ Changing Ps to dinear scale $r_{s} = 10^{-3/10} = 0.5 \times 10^{-3} W$ $\rightarrow \left(\frac{\gamma c}{\kappa c_{\Lambda}}\right)^{2} r_{s}^{2}$ $= \left(\underbrace{\frac{0.85 \times 1.6 \times 10^{-19} \times 1.55 \times 10^{-6}}{6.62 \times 10^{-34} \times 3 \times 10^{8}}}_{6 \times 10^{-34} \times 3 \times 10^{8}} \right)^{2} \left(0.5 \times 10^{-3} \right)^{2}$ -> <u>4LT</u> Ro = 4×1,33×10²³×300 50 (1.06) × (0.5×10)2 0.2809×10-6 - 33.12 × 10-23 $2c\left(\frac{ne}{bcl}\right)l_s$ $\frac{S}{N} = \frac{0.2869 \times 10^{6}}{(1.696 + 3.312)10^{-22} \times 20 \times 10^{9}}$ 2×1.6×10-19×(1.06) × 0.5×103 2 2 0.028045 × 106 1-696 × 10-22 2 = 10 log (0.028045 × 10) = 44.47 dB ____

3.2) At temperature o'C pe. 273K,

$$\frac{S}{N} = \frac{\left(\frac{Ne}{hC/n}\right)^2 P_s^2}{\left(\frac{2e\left(\frac{Ne}{hG_n}\right)^2 S + \frac{4kT}{R_c}\right) \Delta f}}$$

$$\rightarrow \frac{4 \text{ RT}}{R_c}$$

$$= \frac{4 \times 1.38 \times 10^{-23} \times 273}{S0}$$

$$= 30.13 \times 10^{-23}$$

Plugging values from the prop previous part of the question:

$$\frac{S}{N} = \frac{0.2809 \times 10^{-6}}{(1.696 + 3.013) 20 \times 10^{9} \times 10^{-22}}$$

= 0.02982 × 10⁶
= 10 log (0.02982 × 10⁶)
$$\frac{S}{N} = \frac{44.74}{48}$$

3.3) From 3.1 6 3.2 questions, we note that at 300K, SNR = 44.47dB at 273K, SNR2 44.74dB with decreasing temperature, SNR is increasing. ratio will decrease. where of is the bandwidth, If the bandwidth increases, the noise will increase. ... If the bandwidth increases, the signal to noise ratio will decrease.

Zr (irodictive) = 50ns 4 Znr (non-radiative) = 75ms . the internal efficiency Nint = 1/2n 1/2+1/2n 1/50 1/50 + 1/75 2 = 0.6 >= 450mm I = 300 m A Cz 3x10^sm/s hz 6.62x10⁻³⁴Js Cz1.6x10⁻¹⁹ Spie IAC is the enternal efficiency Nort = P/hr I/e

For extraction efficiency, we know that: $\eta = \eta_{int} \times K \times \left[I - \left(\frac{n-1}{n+1} \right) \right] 2 \overline{n} \left(I - \cos \theta_c \right)$ where Nint is the internal efficiency 1. F. D.6 K is absorption loss n is refractive inder 1.e. 3.6 Oc is critical angle. Oc = sin (1) A Q o the C 2 16-12 Griven that remiconductor material is not dight absorbing. . K=1 $\frac{1}{2} = \frac{1}{2} \frac{$ = 0.0077 2 0.77%